

In the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing Of Claims:

1. (Original) A semiconductor component, comprising:

 a semiconductor substrate;

 a covering layer, above a hollow space, made from porous silicon material, wherein the covering layer includes a first section and a second section, a first earlier pore structure of the first section differing from a second earlier pore structure of the second section.

2. (Original) The semiconductor component of claim 1, wherein the semiconductor component includes a pressure sensor.

3. (Original) The semiconductor component of claim 1, wherein the first earlier pore structure in the first section is oriented substantially perpendicularly to a main substrate plane, and the second earlier pore structure in the second section is oriented substantially in parallel to the main substrate plane.

4. (Original) The semiconductor component of claim 1, wherein one of the second earlier pore structure in the second section is provided as a mesoporous structure, the second earlier pore structure in the second section is provided as a nanoporous structure, and the pore structure in the second section has a higher porosity than in the first section.

5. (Original) The semiconductor component of claim 1, wherein the semiconductor substrate includes silicon.

6. (Original) The semiconductor component of claim 1, further comprising: a diaphragm layer above the covering layer.

7. – 10. (Canceled)